HIGH-SPEED 2.5V 512K x 36

IDT70T3539M

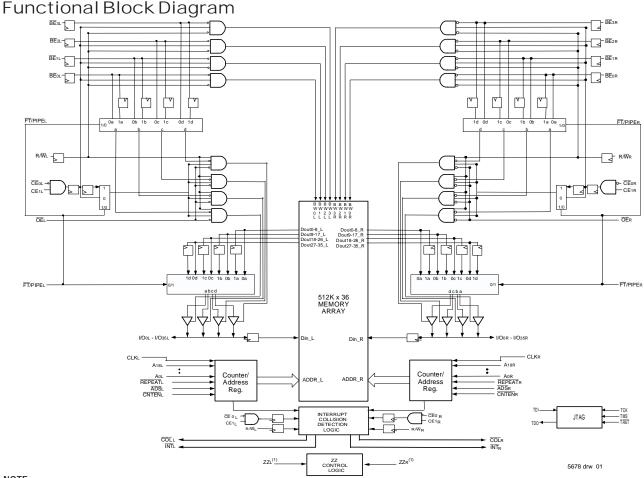
512K x 36 SYNCHRONOUS DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 3.6ns (166MHz)/4.2ns (133MHz)(max.)
 - Industrial: 4.2ns (133MHz) (max.)
- * Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Interrupt and Collision Detection Flags
- Full synchronous operation on both ports
 - 6ns cycle time, 166MHz operation (12Gbps bandwidth)
 - Fast 3.6ns clock to data out
 - 1.5ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 166MHz

- Data input, address, byte enable and control registers
 Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output Mode
- 2.5V (±100mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- Includes JTAG functionality
- Industrial temperature range (-40°C to +85°C) is available at 133MHz
- Available in a 256-pin Ball Grid Array (BGA)
- Green parts available, see ordering information



NOTE:

1. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. FEBRUARY 2018

Description:

The IDT70T3539M is a high-speed 512K x 36 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70T3539M has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70T3539M can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) is at 2.5V.

Pin Configuration (1,2,3,4)

70T3539M BC BC-256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A13 A14 A15 Δ1 A2 A3 A4 A5 A6 Α7 A8 Α9 A10 A11 A12 A16 TDI NC A11L A8L BE_{2L} CE1L OEL CNTENL NC A17L A14L A5L A2L AOL NC NC B1 B2 B3 B4 B5 B6 B7 B8 B9 B10 B11 B12 B13 B14 B15 B16 TDO **BE**3L CEOL REPEATL I/O18L NC A18L A12L A9L R/₩L A4L A1L I/O17L NC A15L Vdd C1 C2 СЗ C4 25 26 C7 C8 C9 C10 C11 C12 C13 C14 C15 C16 I/O18R I/O19L A13L **BE**1L BEOL CLK∟ ADSL Vss A16L A10L A7L A6L АзL **OPTL** I/O17R I/O16L D1 D2 D3 D5 D6 D7 D8 D9 D10 D11 D12 D13 D14 D15 D16 D4 I/O19R I/O20R I/O20L PIPE/FTL Vddql Vddqi Vddqf VDDQR VDDQ VDDQL Vddqr Vddqr Vdd I/O15R I/O15L I/O16R E4 F5 E6 E8 E9 E10 E11 E12 E13 E14 E16 E1 E2 E3 -7 E15 **I/O**21R I/O21L I/O22L VDDQL Vdd ĪNT∟ Vdd Vss Vss Vddqr I/O13L I/O14R Vss VDD Vdd I/O14L F2 -10 F14 F15 F16 F3 F4 -5 F6 F7 F8 F9 F11 F12 F13 COL I/O23L I/O22R I/O23R Vddql Vdd NC I/O12R I/O13R I/O12L Vss Vss Vss Vddqr Vss Vdd G1 G2 G4 G5 G6 G8 G15 G16 G3 G7 G9 G10 G11 G12 G13 G14 I/O24R I/O24L I/O25L VDDQR Vss Vss Vss VDDQL I/O10L I/O11L Vss Vss Vss Vss Vss I/O11R H16 47 H8 Н9 H10 H11 H12 H13 H14 H15 H1 Н2 H3 H4 -15 H6 Vss Vss Vss Vss Vddql I/O9r IO9L I/O10R I/O26R Vddqr I/O26L I/O25R Vss Vss Vss Vss J1 J2 J3 J4 J5 J6 J7 J8 J9 J10 J11 J12 J13 J14 J15 J16 I/O27L I/O28R I/O27R Vddql ZZR Vss Vss Vss Vss Vss Vss ΖZL Vddqr I/O8R I/O7R I/O8L к2 κ4 K6 K8 K12 K13 K15 **<**16 K1 K3 K5 K7 K9 K11 K14 I/O29R I/O29L I/O28L VDDQL Vss Vss Vss Vss Vss Vss Vss Vss VDDQR I/O6R I/O6L I/O7L 8 11 12 15 L2 13 14 15 L6 17 9 .10 ∟13 .14 16 L1 I/O30R COLR Vss Vdd I/O31R VDDQR Vdd NC Vss Vss Vss VDDQL I/O5L I/O4R I/O5R I/O30L M5 M6 М7 M8 М9 M10 M11 M12 M1 M2 M3 M4 M13 M14 M15 M16 I/O32L **INT**R Vdd I/O4L I/O32R I/O31L Vddqr Vdd Vdd Vss Vss Vss Vdd Vddql I/O3R I/O3L N15 N16 N10 N11 N12 **N13** N1 N2 N3 N4 N5 N6 N7 N8 N9 N14 I/O33L P I P E / FT I VDDQF Vddqi Vddqi Vddqf Vddql Vddql Vdd I/O2R I/O34R I/O33R Vddqr Vddqr I/O2L I/O1R P1 P11 P2 P10 P12 P14 P15 P16 P4 77 P8 P9 P13 P6 I/O35R I/O34L TMS A16R A13R **BE**1R BEOR CLKR ADSR I/OOL I/OOR I/O1L A7R A6R Азк A10R R1 R6 R10 R11 R12 R13 R14 R16 R2 RR 39 R15 23 R4 25 **BE**3R CEOR REPEATR I/O35L NC TRST A18R A15R A12R A9R R/WR A4R A1R OPTR NC NC T2 Т4 Т1 T3 T15 Г16 Γ5 Т6 Т7 тя т٩ Г10 T11 T12 T13 T14 NC A17R BE_{2R} NC TCK A14R A11R A8R CE1R ŌĒR CNTENR A5r A2R AOR NC NC

10/07/03

NOTES:

1. All VDD pins must be connected to 2.5V power supply.

2. All VDDC pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).

3. All Vss pins must be connected to ground supply.

4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.

5. This package code is used to reference the package diagram.

6. This text does not indicate orientation of the actual part-marking.

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IDT70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

bus Static RAM Industri

Pin Names

Left Port	Right Port	Names		
CEOL, CE1L	CEOR, CE1R	Chip Enables (Input) ⁽⁵⁾		
R/WL	R/WR	Read/Write Enable (Input)		
ŌĒL	ŌĒR	Output Enable (Input)		
Aol - A18L	A0R - A18R	Address (Input)		
1/Ool - 1/O35l	1/O0r - 1/O35r	Data Input/Output		
CLKL	CLKR	Clock (Input)		
PL/FTL	PL/FTR	Pipeline/Flow-Through (Input)		
ADSL	ADSR	Address Strobe Enable (Input)		
		Counter Enable (Input)		
REPEATL	REPEATR	Counter Repeat ⁽³⁾		
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes) (Input) ⁽⁵⁾		
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾ (Input)		
OPTL	OPTR	Option for selecting VDDOX ^(1,2) (Input)		
ZZL	ZZR	Sleep Mode pin ⁽⁴⁾ (Input)		
	VDD	Power (2.5V) ⁽¹⁾ (Input)		
	Vss	Ground (0V) (Input)		
	TDI	Test Data Input		
	TDO	Test Data Output		
	ТСК	Test Logic Clock (10MHz) (Input)		
TMS		Test Mode Select (Input)		
=	TRST	Reset (Initialize TAP Controller) (Input)		
ĪNTL	ĪNT	Interrupt Flag (Output)		
	COLR	Collision Alert (Output)		

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Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to Vob (2.5V), then that port's I/Os and controls will operate at 3.3V levels and Vobox must be supplied at 3.3V. If OPTx is set to Vss (0V), then that port's I/Os and address controls will operate at 2.5V levels and Vobox must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

3. When REPEAT x is asserted, the counter will reset to the last valid address loaded via ADS x.

4. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. It is recommended that boundry scan not be operated during sleep mode.

 Chip Enables and Byte Enables are double buffered when PL/FT = ViH, i.e., the signals take two cycles to deselect.

IDT70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control (1,2,3,4)

ŌĒ	CLK		CE1	BE 3	BE ₂	BE 1	BE 0	R/W	zz	Byte 3 I/O27-35	Byte 2 I/O18-26	Byte 1 I/O9-17	Byte 0 I/O ₀₋₈	MODE
Х	\uparrow	Н	Х	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	\uparrow	Х	L	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	\uparrow	L	Н	Н	Н	Н	Н	Х	L	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	\uparrow	L	Н	Н	Н	Н	L	L	L	High-Z	High-Z	High-Z	Din	Write to Byte 0 Only
Х	\uparrow	L	Н	Н	Н	L	Н	L	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	\uparrow	L	Н	Н	L	Н	Н	L	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	\uparrow	L	Н	L	Н	Н	Н	L	L	Din	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	\uparrow	L	Н	Н	Н	L	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	\uparrow	L	Н	L	L	Н	Н	L	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	\uparrow	L	Н	L	L	L	L	L	L	Din	Din	Din	Din	Write to All Bytes
L	\uparrow	L	Н	Н	Н	Н	L	Н	L	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	\uparrow	L	Н	Н	Н	L	Н	Н	L	High-Z	High-Z	Dout	High-Z	Read Byte 1 Only
L	\uparrow	L	Н	Н	L	Н	Н	Н	L	High-Z	Dout	High-Z	High-Z	Read Byte 2 Only
L	\uparrow	L	Н	L	Н	Н	Н	Н	L	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	\uparrow	L	Н	Н	Н	L	L	Н	L	High-Z	High-Z	Dout	Dout	Read Lower 2 Bytes Only
L	\uparrow	L	Н	L	L	Н	Н	Н	L	Dout	Dout	High-Z	High-Z	Read Upper 2 Bytes Only
L	\uparrow	L	Н	L	L	L	L	Н	L	Dout	Dout	Dout	Dout	Read All Bytes
Н	\uparrow	Х	Х	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Outputs Disabled
х	Х	Х	Х	Х	Х	Х	Х	Х	Н	High-Z	High-Z	High-Z	High-Z	Sleep Mode

NOTES:

1. $\underline{"H"} = \underline{VIH}, \underline{"L"} = \underline{VIL}, \underline{"X"} = Don't Care.$

2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.

3. $\overline{\text{OE}}$ and ZZ are asynchronous input signals.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Truth Table II—Address Counter Control^(1,2)

Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
х	An	An + 1	\uparrow	Н	L ⁽⁵⁾	Н	D⊮o(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	\uparrow	Н	Н	Н	D⊮o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	\uparrow	Х	Х	L ⁽⁴⁾	Dvo(n)	Counter Set to last valid ADS load

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CEo, CE1, BEn and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. $\overline{\text{ADS}}$ and $\overline{\text{REPEAT}}$ are independent of all other memory control signals including $\overline{\text{CE}}_{0}$, CE1 and $\overline{\text{BE}}_{n}$

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, BEn.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

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Recommended Operating Temperature and Supply Voltage ⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	$0^{\circ}C$ to $+70^{\circ}C$	0V	2.5V <u>+</u> 100mV
Industrial	-40°C to +85°C	0V	2.5V <u>+</u> 100mV
NOTEC			5678 tbl 04

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions with VDD0 at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Vss	Ground	0	0	0	V
Vін	Input High Volltage (Address, Control & Data I/O Inputs) ⁽³⁾	1.7		Vddq + 100mV ⁽²⁾	V
Vін	Input High Voltage - JTAG	1.7		Vdd + 100mV ⁽²⁾	V
Vін	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		Vdd + 100mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.7	V
V⊫	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	V

NOTES:

5678 tbl 05a

5678 tbl 05b

- 1. VIL (min.) = -1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- 2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to $V_{SS}(0V)$, and V_{DDOX} for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDO at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
Vih	Input High Voltage (Address, Control &Data I/O Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V
Vih	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	V
Vін	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		VDD + 100mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3(1)		0.8	V
Vı∟	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	V

NOTES:

1. VIL (min.) = -1.0V for pulse width less than tcyc/2, or 5ns, whichever is less.

2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

 To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VDD (2.5V), and VDDOX for that port must be supplied as indicated above.

Absolute Maximum Ratings (1)

Symbol	Rating	Commercial & Industrial	Unit
Vterm (Vdd)	VDD Terminal Voltage with Respect to GND	-0.5 to 3.6	V
Vterm ⁽²⁾ (Vddq)	VDDQ Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
V _{TERM⁽²⁾ (INPUTS and I/O's)}	Input and I/O Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
Tbias ⁽³⁾	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ит	Junction Temperature	+150	٥C
IOUT(For VDDQ = 3.3V)	DC Output Current	50	mA
IOUT(For VDDQ = 2.5V)	DC Output Current	40	mA
NOTES			5678 tbl 0

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any Input or I/O pin cannot exceed VDDo during power supply ramp up.
- 3. Ambient Temperature under DC Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

(TA = +25°C, F = 1.0MHz) BGA ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 0V	15	рF
Cout ⁽³⁾	Output Capacitance	Vout = 0V	10.5	pF
				5678 tbl 07

NOTES:

 These parameters are determined by device characterization, but are not production tested.

2. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($VDD = 2.5V \pm 100mV$)

			70T35	39MS	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., V IN = 0 V to V DDQ	_	10	μA
lu	JTAG & ZZ Input Leakage Current ^(1,2)	$V_{DD} = Max., V_{IN} = 0V$ to V_{DD}	_	±30	μA
Ilo	Output Leakage Current ^(1,3)	$\overline{CE}{0}$ = VIH or CE1 = VIL, VOUT = 0V to VDDQ	_	10	μA
Vol (3.3V)	Output Low Voltage ⁽¹⁾	IOL = +4mA, $VDDQ = Min$.	_	0.4	V
Voн (3.3V)	Output High Voltage ⁽¹⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽¹⁾	IOL = +2mA, $VDDQ = Min$.	_	0.4	V
Voн (2.5V)	Output High Voltage ⁽¹⁾	IOH = -2mA, $VDDQ = Min$.	2.0	_	V

NOTES:

2. Applicable only for TMS, TDI and TRST inputs.

3. Outputs tested in tri-state mode.

^{1.} VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}$ (VDD = 2.5V ± 100mV)

						9MS166 Only	Co	9MS133 m'l nd	
Symbol	Parameter	Test Condition	Versio	on	Тур. ⁽⁴⁾	Мах.	Typ. ⁽⁴⁾	Мах.	Uni
IDD	Dynamic Operating	\overline{CE}_{L} and $\overline{CE}_{R}=$ VIL,	COM'L	S	640	900	520	740	
	Current (Both Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S	_	_	520	900	mA
ISB1 ⁽⁶⁾	Standby Current	$\overline{CE}L = \overline{CE}R = VIH$	COM'L	S	350	460	280	380	
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S	_	_	280	470	m/
ISB2 ⁽⁶⁾	Standby Current (One Port - TTL	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$	COM'L	S	500	650	400	500	
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	_	_	400	620	m.
ISB3	Full Standby Current	Both Ports CEL and	COM'L	S	12	20	12	20	
	(Both Ports - CMOS Level Inputs)	$\label{eq:certain} \overline{\text{CE}}_{\text{R}} \geq \text{VDDQ} - 0.2\text{V}, \ \text{Vin} \geq \text{VDDQ} - 0.2\text{V} \\ \text{or Vin} \leq 0.2\text{V}, \ \text{f} = 0^{(2)} \\ \end{array}$	IND	S	_		12	25	m.
ISB4 ⁽⁶⁾	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$	COM'L	S	500	650	400	500	
	(One Port - CMOS Level Inputs)	$VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$ Active Port, Outputs Disabled, f = fMAX ⁽¹⁾	IND	S	_	_	400	620	m
lzz	Sleep Mode Current	ZZL = ZZR = VIH f=fMAX ⁽¹⁾	COM'L	S	12	20	12	20	
	(Both Ports - TTL Level Inputs)	I=IMAX`'	IND	S			12	25	m

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS".

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 2.5V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 30mA (Typ).

5. $\overline{CEx} = V_{IL}$ means $\overline{CEox} = V_{IL}$ and $CE_{1X} = V_{IH}$ $\overline{CEx} = V_{IH}$ means $\overline{CEox} = V_{IH}$ or $CE_{1X} = V_{IL}$

 $\overline{\text{CE}}x \leq 0.2V$ means $\overline{\text{CE}}\textsc{ox} \leq 0.2V$ and $\text{CE}\textsc{ix} \geq V\textsc{dd}$ - 0.2V

 $\overline{\text{CE}}\text{x} \geq \text{V}\text{DDQ}$ - 0.2V means $\overline{\text{CE}}\text{ox} \geq \text{V}\text{DDQ}$ - 0.2V or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.

6. ISB1, ISB2 and ISB4 will all reach full standby levels (ISB3) on the appropriate port(s) if ZZL and/or ZZR = VIH.

IDT70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	1.5V/1.25V
Output Reference Levels	1.5V/1.25V
Output Load	Figure 1

5678 tbl 10

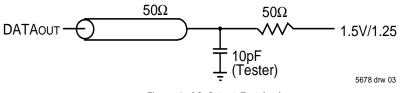
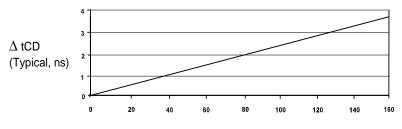


Figure 1. AC Output Test load.



 Δ Capacitance (pF) from AC Test Load 5678 drw 04

High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(2,3)}$ (VDD = 2.5V ± 100mV, TA = 0°C to +70°C)

		70T353 Com'	9MS166 I Only	70T353 Cc &	9MS133 om'l Ind	
Symbol	Parameter	Min.	Max.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	20		25	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	6	_	7.5	-	ns
tcн1	Clock High Time (Flow-Through) ⁽¹⁾	8		10	-	ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	8		10		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2.4		3		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.4		3		ns
tsa	Address Setup Time	1.7		1.8		ns
tha	Address Hold Time	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5		0.5		ns
tsв	Byte Enable Setup Time	1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5		0.5		ns
tsw	R/W Setup Time	1.7		1.8		ns
tHW	R/W Hold Time	0.5		0.5		ns
tsp	Input Data Setup Time	1.7		1.8		ns
thd	Input Data Hold Time	0.5		0.5		ns
tsad	ADS Setup Time	1.7		1.8		ns
thad	ADS Hold Time	0.5		0.5		ns
tscn	CNTEN Setup Time	1.7		1.8		ns
then	CNTEN Hold Time	0.5		0.5		ns
İ SRPT	REPEAT Setup Time	1.7		1.8		ns
I HRPT	REPEAT Hold Time	0.5		0.5		ns
toe	Output Enable to Data Valid		4.4		4.6	ns
tolz ⁽⁶⁾	Output Enable to Output Low-Z	1		1		ns
tонz ⁽⁶⁾	Output Enable to Output High-Z	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		3.6		4.2	ns
tDC	Data Output Hold After Clock High	1		1		ns
tскнz ⁽⁶⁾	Clock High to Output High-Z	1	3.6	1	4.2	ns
tcklz ⁽⁶⁾	Clock High to Output Low-Z	1		1		ns
tins	Interrupt Flag Set Time		7	—	7	ns
tinr	Interrupt Flag Reset Time		7	—	7	ns
tcols	Collision Flag Set Time		3.6	—	4.2	ns
COLR	Collision Flag Reset Time		3.6		4.2	ns
tzzsc	Sleep Mode Set Cycles	2		2		cycles
tzzrc	Sleep Mode Recovery Cycles	3		3		cycles
Port-to-Port	Delay	I		•		
tco	Clock-to-Clock Offset	5		6		ns
OFS	Clock-to-Clock Offset for Collision Detection	Please refe				

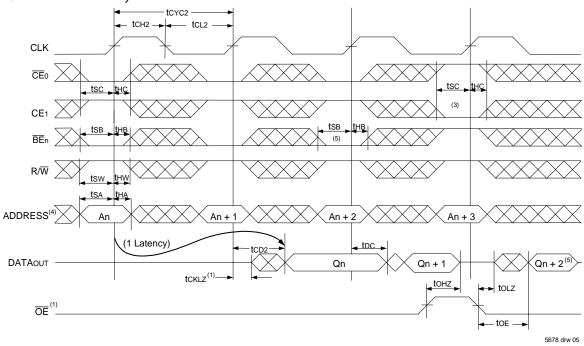
1. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when FT/PIPEx = Vbb (2.5V). Flow-through parameters (tcvc1, tcb1) apply when $\overline{FT}/PIPE = Vss$ (0V) for that port.

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPE and OPT. FT/PIPE and OPT should be treated as DC signals, i.e. steady state during operation.

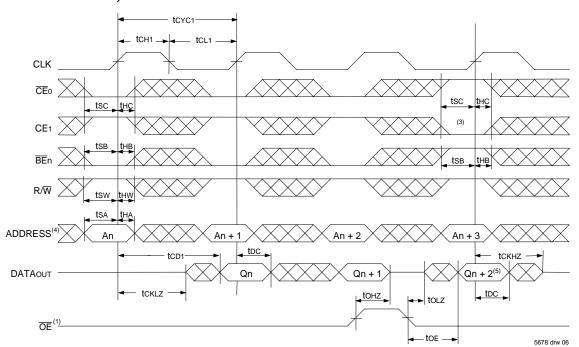
3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 6 for details on selecting the desired operating voltage levels for each port.

4. Guaranteed by design (not production tested).



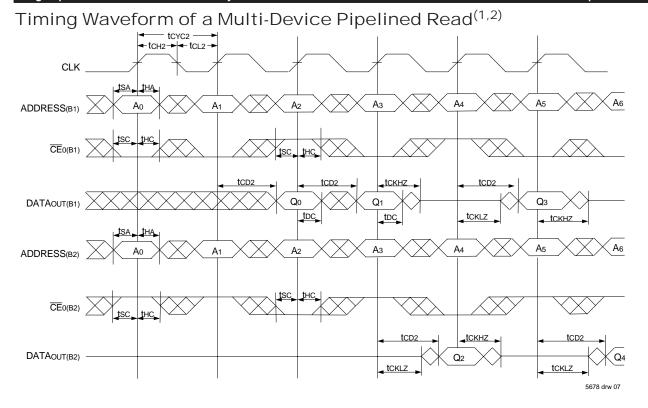


Timing Waveform of Read Cycle for Flow-through Output $(FT/PIPE"x" = VIL)^{(1,2,6)}$

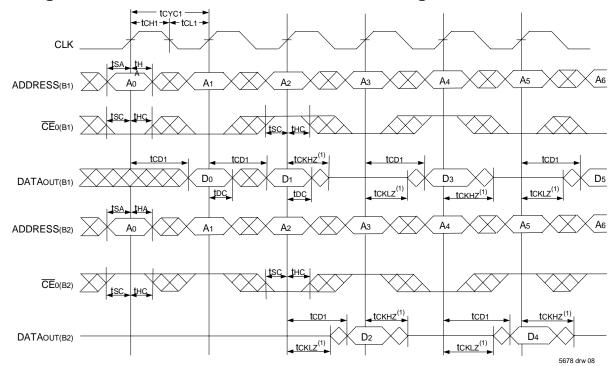


- 1. DE is asynchronously controlled; all other inputs depicted in the above waveforms are synchronous to the rising clock edge.
- 2. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{REPEAT} = VIH$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, $\overline{BE}_n = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.

Industrial and Commercial Temperature Ranges

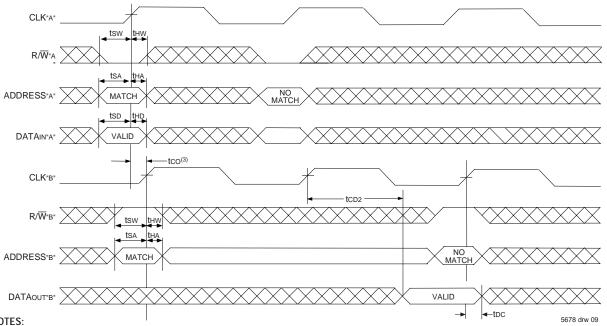


Timing Waveform of a Multi-Device Flow-Through Read^(1,2)



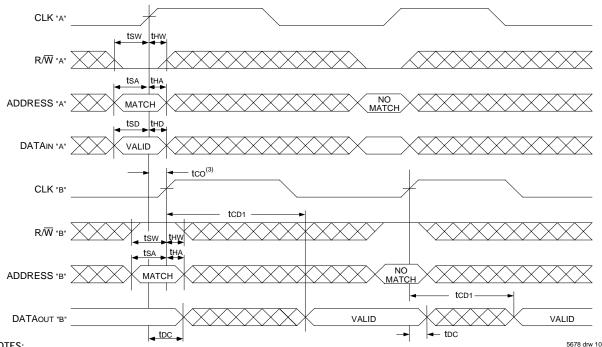
- B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70T3539M for this waveform, 1.
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation. 2. BEn, OE, and ADS = VIL; CE1(B1), CE1(B2), R/W, CNTEN, and REPEAT = VIH.

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2,4)



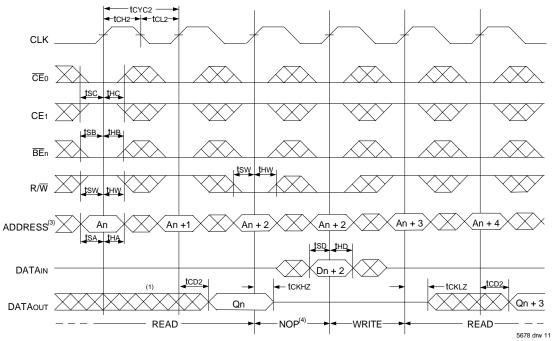
- NOTES:
- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco < minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be $tco + tcyc_2 + tcp_2$).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read^(1,2,4)



- 1. \overline{CE}_{0} , \overline{BE}_{n} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcvc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcD1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

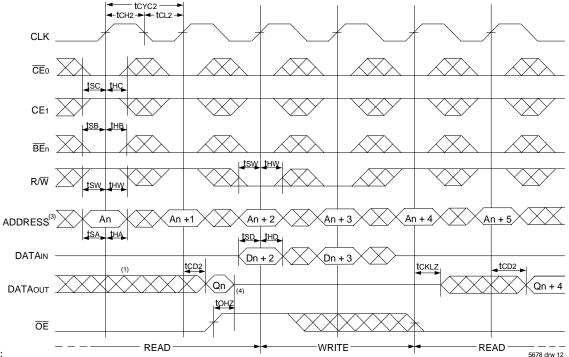
Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



NOTES:

- Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
 CE0, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers 3. are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

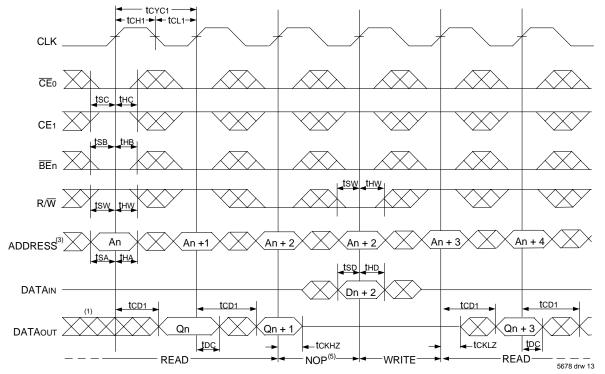


NOTES:

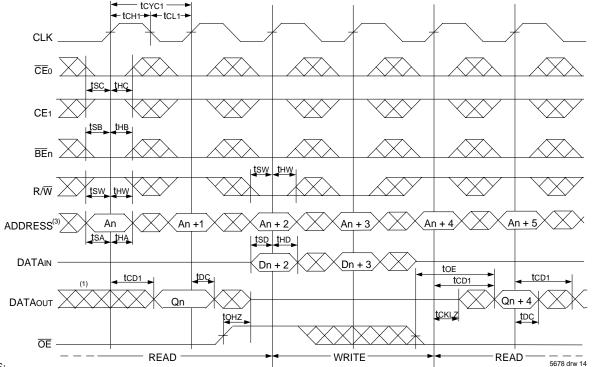
1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

- 2. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference 3. use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽²⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

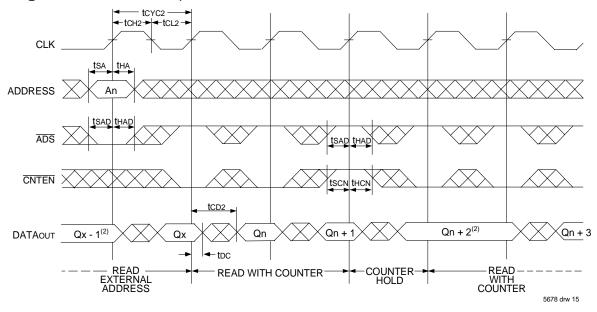
1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

2. TEO, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

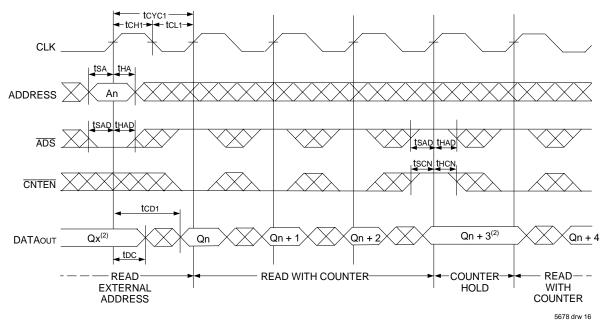
3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

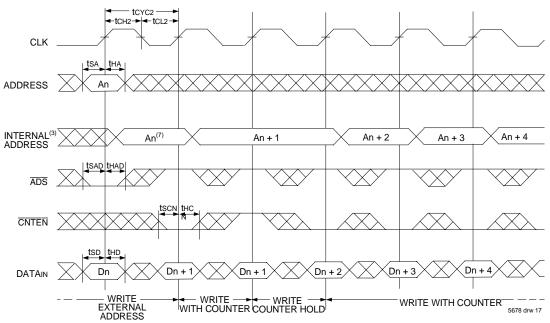


NOTES:

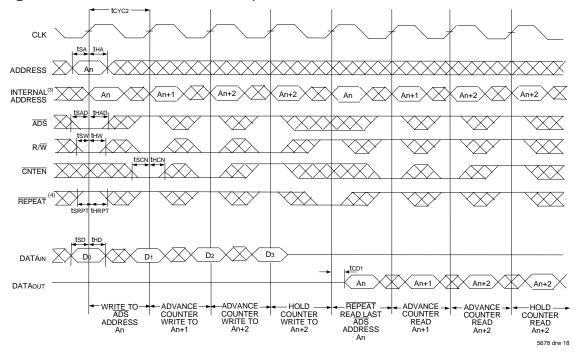
1. \overline{CE}_{0} , \overline{OE} , \overline{BE}_{n} = VIL; CE1, R/W, and \overline{REPEAT} = VIH.

2. If there is no address change via $\overline{\text{ADS}} = \text{VIL}$ (loading a new address) or $\overline{\text{CNTEN}} = \text{VIL}$ (advancing the address), i.e. $\overline{\text{ADS}} = \text{VIH}$ and $\overline{\text{CNTEN}} = \text{VIH}$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



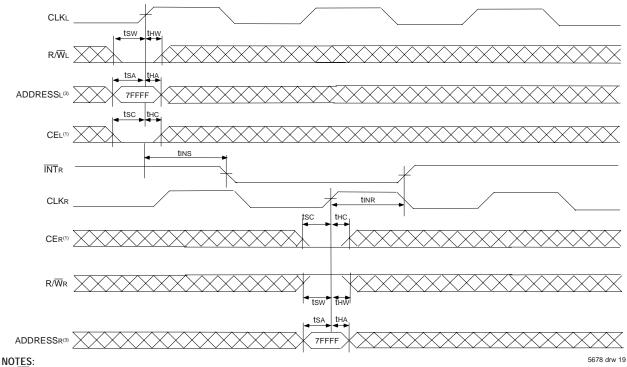
Timing Waveform of Counter Repeat^(2,6)



- 1. $\overline{CE_0}$, $\overline{BE_n}$, and $R/\overline{W} = V_{IL}$; CE1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE}_{0} , $\overline{BE}_{n} = V_{IL}$; $CE_{1} = V_{IH}$.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$. 4. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. For more information on REPEAT function refer to Truth Table II.
- 5. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.

5678 tbl 12

Waveform of Interrupt Timing⁽²⁾



- 1. CE0 = VIL and CE1 = VIH
- 2. All timing is the same for Left and Right ports.
- 3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

				Right Port						
CLK∟	R/₩ L ⁽²⁾	CEL ⁽²⁾	A18L-A0L	ĪNTL	CLKr	R/ W R ⁽²⁾	CER ⁽²⁾	A18R-A0R	ĪNTR	Function
Ŷ	L	L	7FFFF	Х	Ŷ	Х	Х	Х	L	Set Right INTR Flag
Ŷ	Х	Х	Х	Х	Ŷ	Н	L	7FFFF	Н	Reset Right INTR Flag
Ŷ	Х	Х	Х	L	Ŷ	L	L	7FFFE	Х	Set Left INTL Flag
Ŷ	Н	L	7FFFE	Н	Ŷ	Х	Х	Х	Х	Reset Left INTL Flag

Truth Table III — Interrupt Flag⁽¹⁾

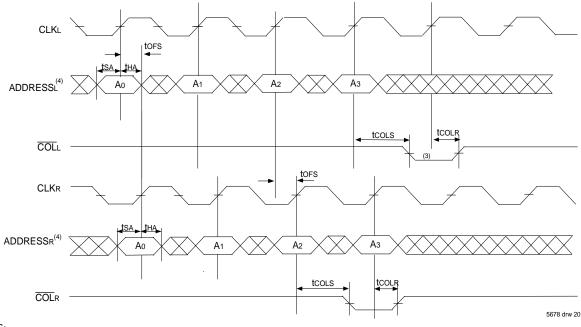
NOTES:

1. INTL and INTR must be initialized at power-up by Resetting the flags.

2. CE0 = VIL and CE1 = VIH. R/W and CE are synchronous with respect to the clock and need valid set-up and hold times.

3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

Waveform of Collision Timing^(1,2)



NOTES:

2. For reading port, OE is a Don't care on the Collision Detection Logic. Please refer to Truth Table IV for specific cases.

3. Leading Port Output flag might output 3tcyc2 + tcoLs after Address match.

4. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

Collision Detection Timing^(3,4)

Cuelo Timo	tors (ns)					
Cycle Time	Region 1 (ns) ⁽¹⁾	Region 2 (ns) ⁽²⁾				
5ns	0 - 2.8	2.81 - 4.6				
6ns	0 - 3.8	3.81 - 5.6				
7.5ns	0 - 5.3	5.31 - 7.1				

NOTES:

- 1. Region 1
- Both ports show collision after 2nd cycle for Addresses 0, 2, 4 etc. 2. Region 2

Leading port shows collision after 3rd cycle for addresses 0, 3, 6, etc. while trailing port shows collision after 2nd cycle for addresses 0, 2, 4 etc.

5678 tbl 14

3. All the production units are tested to midpoint of each region.

4. These ranges are based on characterization of a typical device.

Truth Table IV — Collision Detection Flag

		Left Port			Right Port					
CLKL	R/WL ⁽¹⁾	CEL ⁽¹⁾	A18L-A0L ⁽²⁾	COLL	CLKr	R/ W R ⁽¹⁾	CER ⁽¹⁾	A18R-A0R ⁽²⁾	COLR	Function
¢	Н	L	MATCH	Н	Ŷ	Н	L	MATCH	Н	Both ports reading. Not a valid collision. No flag output on either port.
¢	Н	L	MATCH	L	Ŷ	L	L	MATCH	Н	Left port reading, Right port writing. Valid collision, flag output on Left port.
¢	L	L	MATCH	Н	Ŷ	Н	L	MATCH	L	Right port reading, Left port writing. Valid collision, flag output on Right port.
¢	L	L	MATCH	L	Ŷ	L	L	MATCH	L	Both ports writing. Valid collision. Flag output on both ports.

19

NOTES:

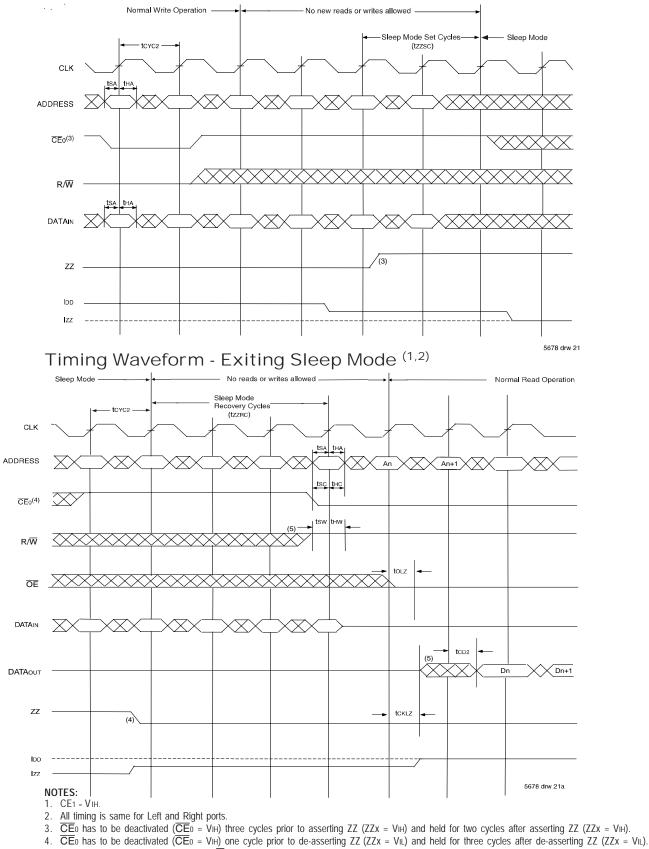
1. $\overline{CE}_0 = V_{IL}$ and $CE_1 = V_{IH}$. R/\overline{W} and CE are synchronous with respect to the clock and need valid set-up and hold times.

2. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

^{1.} $\overline{CE}_0 = V_{IL}, CE_1 = V_{IH}.$

⁵⁶⁷⁸ tbl 13

Timing Waveform - Entering Sleep Mode (1,2)



5. The device must be in Read Mode (R/W High) when exiting sleep mode. Outputs are active but data is not valid until the following cycle.

IDT70T3539M

High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Functional Description

The IDT70T3539M provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse width is independent of the cycle time.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70T3539Ms for depth expansion configurations. Two cycles are required with \overline{CE} LOW and CE1 HIGH to re-activate the outputs.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 7FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table. The left port clears the interrupt through access of address location 7FFFE when $\overline{CEL} = VIL$ and $R/\overline{WL} = VIH$. Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 7FFFF. The message (36 bits) at 7FFFE or 7FFFF is user-defined since it is an addressable SRAMIocation. If the interrupt function is not used, address locations 7FFFE and 7FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Collision Detection

Collision is defined as an overlap in access between the two ports resulting in the potential for either reading or writing incorrect data to a specific address. For the specific cases: (a) Both ports reading - no data is corrupted, lost, or incorrectly output, so no collision flag is output on either port. (b) One port writing, the other port reading port might capture data that is in a state of transition and hence the reading port's collision flag is output. (c) Both ports writing - there is a risk that the two ports will interfere with each other, and the data stored in memory will not be a valid write from either port (it may essentially be a random combination of the two). Therefore, the collision flag is output on both ports. Please refer to Truth Table IV for all of the above cases.

The alert flag (COL_x) is asserted on the 2nd or 3rd rising clock edge of the affected port following the collision, and remains low for one cycle. Please refer to Collision Detection Timing Table on Page 19. During that next cycle, the internal arbitration is engaged in resetting the alert flag (this avoids a specific requirement on the part of the user to reset the alert flag). If two collisions occur on subsequent clock cycles, the second collision may not generate the appropriate alert flag. A third collision will generate the alert flag as appropriate. In the event that a user initiates a burst access on both ports with the same starting address on both ports and one or both ports writing during each access (i.e., imposes a long string of collisions on contiguous clock cycles), the alert flag will be asserted and cleared every other cycle. Please refer to the Collision Detection timing waveform on Page 19.

Collision detection on the IDT70T3539M represents a significant advance in functionality over current sync multi-ports, which have no such capability. In addition to this functionality the IDT70T3539M sustains the key features of bandwidth and flexibility. The collision detection function is very useful in the case of bursting data, or a string of accesses made to sequential addresses, in that it indicates a problem within the burst, giving the user the option of either repeating the burst or continuing to watch the alert flag to see whether the number of collisions increases above an acceptable threshold value. Offering this function on chip also allows users to reduce their need for arbitration circuits, typically done in CPLD's or FPGA's. This reduces board space and design complexity, and gives the user more flexibility in developing a solution.

Sleep Mode

The IDT70T3539M is equipped with an optional sleep or low power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode.

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZx = VIH) and three cycles after de-asserting ZZ (ZZx = VIH), the device must be disabled via the chip enable pins. If a write or read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode (R/Wx = VIH) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue torun without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

IDT70T3539M

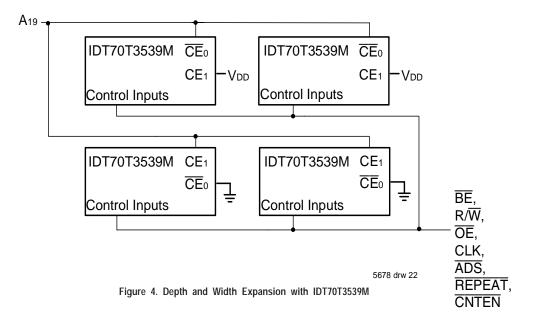
High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Depth and Width Expansion

The IDT70T3539M features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70T3539M can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 72-bits or wider.



JTAG Functionality and Configuration

The IDT70T3539M is composed of two independent memory arrays, and thus cannot be treated as a single JTAG device in the scan chain. The two arrays (A and B) each have identical characteristics and commands but must be treated as separate entities in JTAG operations. Please refer to Figure 5.

JTAG signaling must be provided serially to each array and utilize the information provided in the Identification Register Definitions, Scan

Register Sizes, and System Interface Parameter tables. Specifically, commands for Array B must precede those for Array A in any JTAG operations sent to the IDT70T3539M. Please reference Application Note AN-411, "JTAG Testing of Multichip Modules" for specific instructions on performing JTAG testing on the IDT70T3539M. AN-411 is available at www.idt.com.

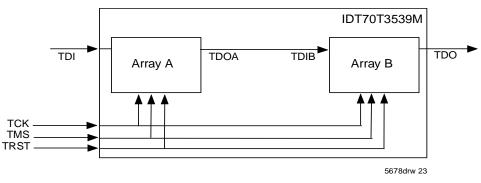
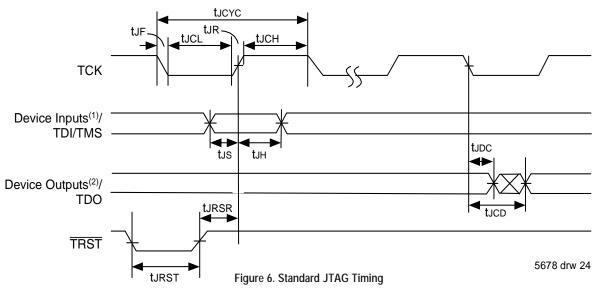


Figure 5. JTAG Configuration for IDT70T3539M

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, and TRST.

2. Device outputs = All device outputs except TDO.

		-		
Symbol	Parameter	Min.	Мах.	Units
ticyc	JTAG Clock Input Period	100		ns
исн	JTAG Clock HIGH	40		ns
ticl	JTAG Clock Low	40		ns
U R	JTAG Clock Rise Time		3(1)	ns
t)F	JTAG Clock Fall Time		3(1)	ns
URST	JTAG Reset	50		ns
URSR	JTAG Reset Recovery	50	_	ns
ticd	JTAG Data Output		25	ns
tudo	JTAG Data Output Hold	0		ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

1. Guaranteed by design.

2. 30pF loading on external output signals.

3. Refer to AC Electrical Test Conditions stated earlier in this document.

4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

BYPASS	1111111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	00100010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	01000100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers except $\overline{\text{INTx}}$ and $\overline{\text{COLx}}$ to a High-Z state.
CLAMP	00110011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	00010001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	01010101, 01110111, 10001000, 10011001, 10101010, 10111011, 11001100	Several combinations are reserved. Do not use codes other than those identified above.
PRIVATE	01100110, 11101110, 11011101	For internal use only.

EXTEST 00000000

Instruction

System Interface Parameters

Register Name	Bit Size Array A	Bit Size Array B	Bit Size 70T3539M	
Instruction (IR)	4	4	8	
Bypass (BYR)	1	1	2	
Identification (IDR)	32	32	64	
Boundary Scan (BSR)	Note (3)	Note (3)	Note (3)	
			5678 tbl 17	

Code

ID Register Indicator Bit (Bit 32)

Scan Register Sizes

IDT Device ID (27:12)

IDT JEDEC ID (11:1)

ID Register Indicator Bit (Bit 0)

Instruction Field Array B	Value Array B	Instruction Field Array A	Va Arra
Revision Number (31:28)	0x0	Revision Number (63:60)	0)

1

IDT70T3539M High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Identification Register Definitions

Industrial and Commercial Temperature Ranges

Indicates the presence of an ID Register

Description

Forces contents of the boundary scan cells onto the device outputs⁽¹⁾.

Places the boundary scan register (BSR) between TDI and TDO.

5678 tbl 18

NOTES:

1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, and TRST.

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

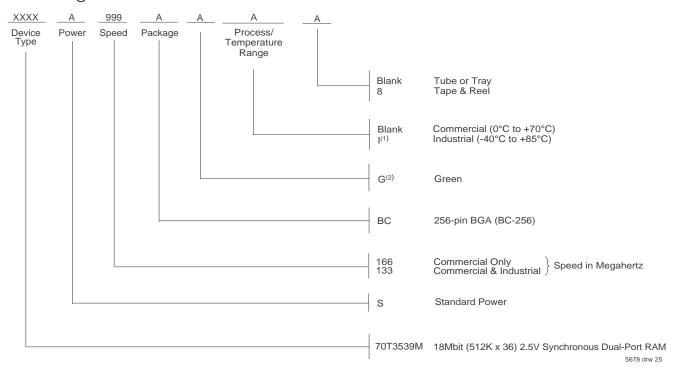
Value Value Instruction Field Array A Description ray A 0x0 Reserved for Version number 0x333 IDT Device ID (59:44) 0x333 Defines IDT Part number 0x33 IDT JEDEC ID (43:33) 0x33 Allows unique identification of device vendor as IDT

1

IDT70T3539M

High-Speed 2.5V 512K x 36 Dual-Port Synchronous Static RAM

Ordering Information



NOTES:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your sales office.

LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

IDT Clock Solution for IDT70T3539M Dual-Port

	Dual-Port I/O	Specitications		Clock Specif	IDT	IDT		
IDT Dual-Port Part Number	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device
70T3539M	3.3/2.5	LVTTL	15pF	40%	166	75ps	5T2010	5T9010 5T905, 5T9050 5T907, 5T9070

Datasheet Document History:

10/08/03:	Initial Datasheet							
10/20/03:	Page 1 Added "Includes JTAG functionality" to features							
	Page 25 Added IDT Clock Solution Table							
12/04/03:	Page 10 Added tops symbol and parameter to AC Electrical Characteristics table							
	Page 19 Updated Collision Timing waveform							
	Page 19 Added Collision Detection Timing table and footnotes							
	Page 22 Added JTAG Configuration and JTAG Functionality descriptions							
02/02/04:	Page 8 Changed IsB3 and Izz in the DC Electrical Characteristics table							
04/08/04:	Page 20 & 21 Clarified Sleep Mode Text and Waveform							
	Page 22 Added an Application Note, AN-411, reference to the JTAG Functionality and Configuration text							
	Page 4 Added another sentence to footnote 4 to recommend that boundary scan not be operated during sleep mode							
05/28/04:	Removed "Preliminary" status							
07/25/08:	Page 8 Corrected a typo in the footnotes of the DC Chars table							
01/29/09:	Page 25 Removed "IDT" from orderable part number							
02/04/10:	Page 7 Corrected the Capacitance Table Title							
05/15/15:	Page 1 Added Green parts availability to features							
	Page 26 Added Tape and Reel and Green indicators with their footnote annotations to the Ordering Information							
02/13/18:	Product Discontinuation Notice - PDN# SP-17-02							
	Last time buy expires June 15, 2018							



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for Tech Support: 408-284-2794 DualPortHelp@idt.com

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 70T3539MS133BCI
 70T3539MS133BC8

 70T3539MS166BCG
 70T3539MS166BC8
 70T3539MS133BCGI
 70T3539MS166BC6
 70T3539MS166BC6